STB80NF03L-04T-1
STB80NF03L-04T

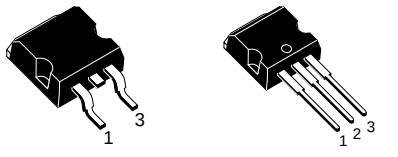
N-CHANNEL 30 V - 0.0035Ω - 80A D²PAK/I²PAK
STripFET™II MOSFET

Table 1: General Features

TYPE	V_{DSS}	$R_{DS(on)}$	I_D (1)
STB80NF03L-04T	30 V	< 0.004 Ω	80 A
STB80NF03L-04T-1	30 V	< 0.004 Ω	80 A

- TYPICAL $R_{DS}(on)$ = 0.0035 Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED

Figure 1: Package



D²PAK I²PAK

DESCRIPTION

This MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalance characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING

Figure 2: Internal Schematic Diagram

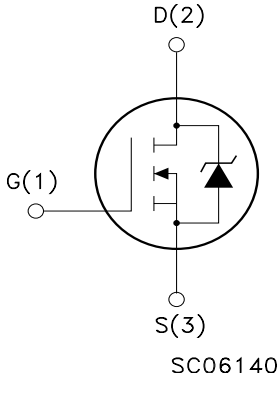


Table 2: Order Codes

Part Number	Marking	Package	Packaging
STB80NF03L-04TT4	B80NF03L-04T	D²PAK	TAPE & REEL
STB80NF03L-04T-1	B80NF03L-04T	I²PAK	TUBE

Table 3: Absolute Maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	30	V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	30	V
V_{GS}	Gate- source Voltage	± 20	V
I_D (#)	Drain Current (continuous) at T_C = 25°C	80	A
I_D (#)	Drain Current (continuous) at T_C = 100°C	80	A
I_{DM} (●)	Drain Current (pulsed)	320	A
P_{TOT}	Total Dissipation at T_C = 25°C	300	W
	Derating Factor	2.0	W/°C
dv/dt (1)	Peak Diode Recovery Voltage Slope	2.0	V/ns
T_{stg}	Storage Temperature	–65 to 175	°C
T_j	Max. Operating Junction Temperature	175	°C

(●) Pulse width limited by safe operating area
(1) $I_{SD} \leq 80A$, $di/dt \leq 300A/\mu s$, V_{DD} =24 V ; $T_j \leq T_{JMAX.}$
(#) Limited by Package

Table 4: Thermal Data

Rthj-case	Thermal Resistance Junction-case Max	0.5	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose	300	°C

Table 5: Avalanche Characteristics

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	40	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 15 V)	2.3	J

ELECTRICAL CHARACTERISTICS (T_{CASE} =25°C UNLESS OTHERWISE SPECIFIED)

Table 6: On /Off

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA, V_{GS} = 0	30			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating			1	µA
		V_{DS} = Max Rating, T_C = 125 °C			10	µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 20V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, I_D = 250µA	1	1.5	2.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10 V, I_D = 40 A		0.0035	0.004	Ω
		V_{GS} = 5 V, I_D = 20 A		0.0065	0.0095	Ω

Table 7: Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	V_{DS} =15 V, I_D = 40 A		100		S
C_{iss}	Input Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		5000		pF
C_{oss}	Output Capacitance			1720		pF
C_{rss}	Reverse Transfer Capacitance			350		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)

Table 8: Switching On

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = 15 V, I_D = 40 A R_G = 4.7Ω V_{GS} = 5.0 V (see test circuit, Figure 3)		40		ns
t_r	Rise Time			300		ns
Q_g	Total Gate Charge	V_{DD} = 15 V, I_D = 80A, V_{GS} = 10V		120	168	nC
Q_{gs}	Gate-Source Charge			25		nC
Q_{gd}	Gate-Drain Charge			40		nC

Table 9: Switching

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off-Delay Time	V_{DD} = 15 V, I_D = 40 A, R_G = 4.7Ω, V_{GS} = 5.0V (see test circuit, Figure 3)		30		ns
t_f	Fall Time			70		ns

Table 10: Source Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				80	A
I_{SDM} (1)	Source-drain Current (pulsed)				320	A
V_{SD} (2)	Forward On Voltage	I_{SD} = 80 A, V_{GS} = 0			1.5	V
t_{rr}	Reverse Recovery Time	I_{SD} = 80 A, di/dt = 100A/µs, V_{DD} = 20 V, T_j = 150°C (see test circuit, Figure 5)		75		ns
Q_{rr}	Reverse Recovery Charge			140		nC
I_{RRM}	Reverse Recovery Current			4		A

(1) The value is rated according $R_{thj\text{-}C}$ and is limited by wire bonding.
(2) When mounted on FR-4 board of 1in², 2oz Cu, t < 10sec

Figure 3: Safe Operating Area

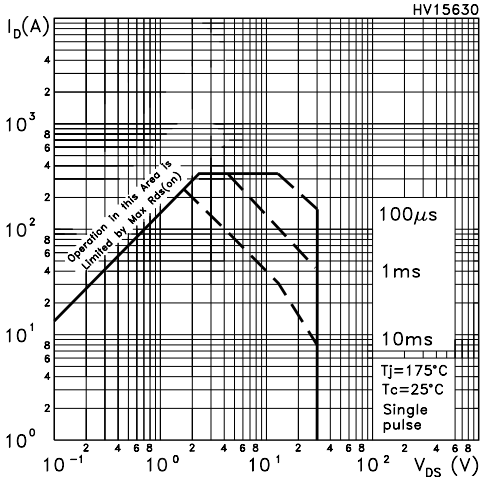


Figure 4: Output Characteristics

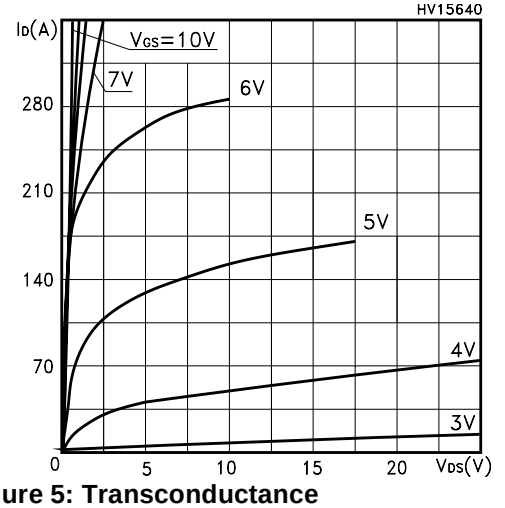


Figure 5: Transconductance

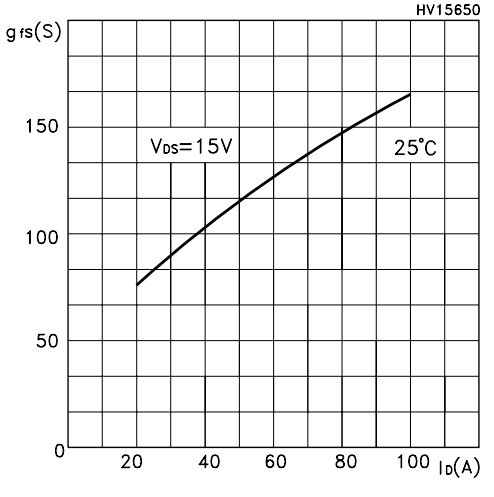


Figure 6: Thermal Impedance

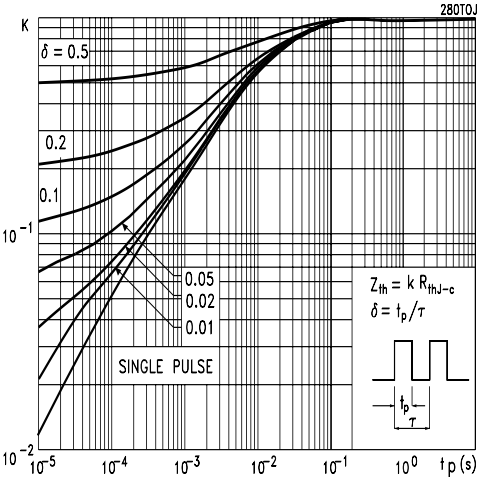


Figure 7: Transfer Characteristics

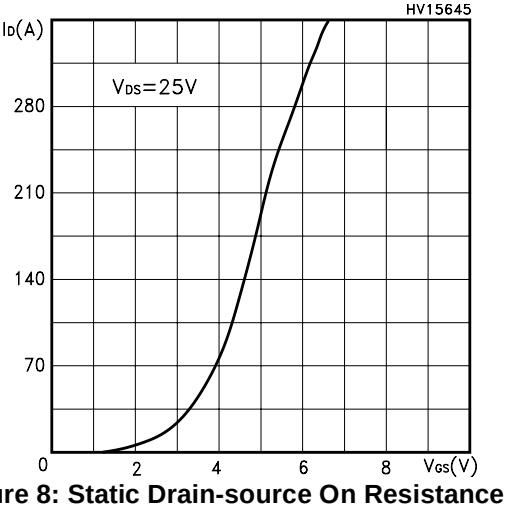


Figure 8: Static Drain-source On Resistance

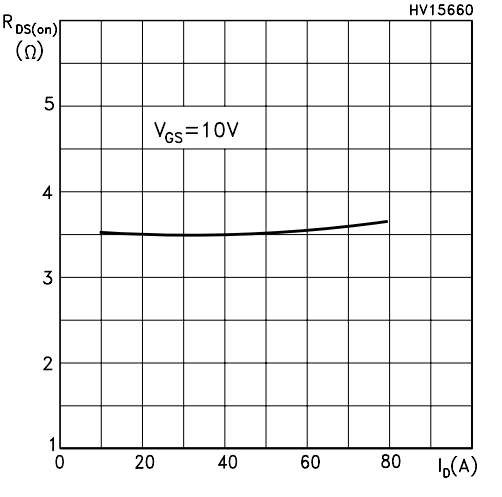


Figure 9: Gate Charge vs Gate-source Voltage

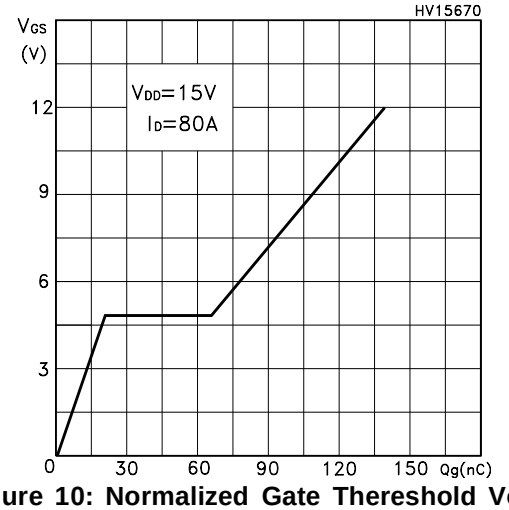


Figure 10: Normalized Gate Thereshold Voltage vs Temperature

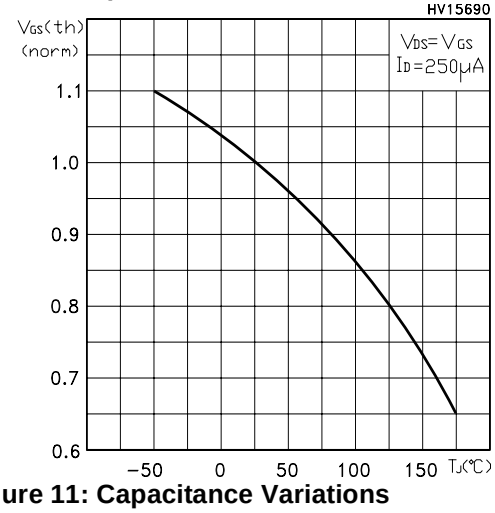


Figure 11: Capacitance Variations

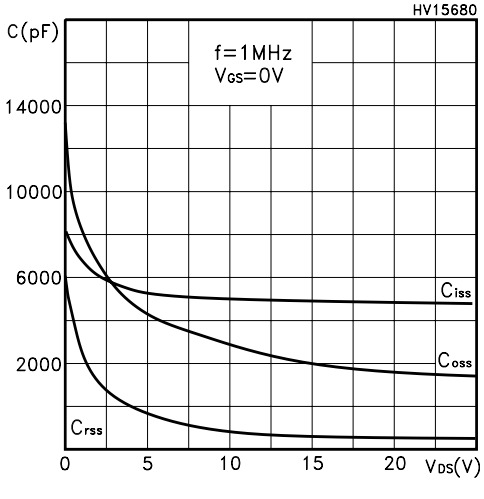


Figure 12: Normalized On Resistance vs Temperature

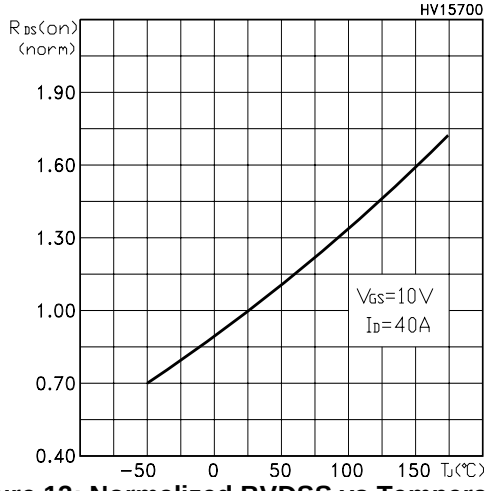


Figure 13: Normalized BVDSS vs Temperature

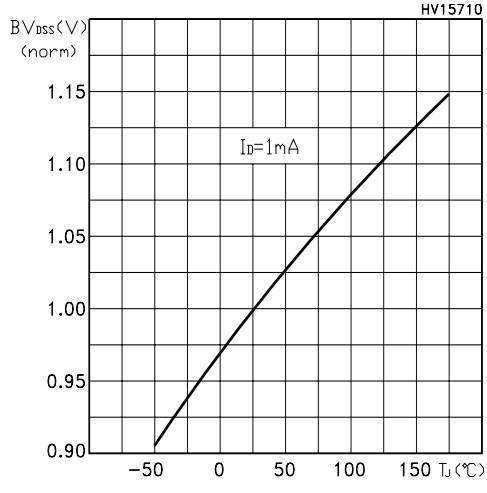


Figure 14: Switching Times Test Circuit For Resistive Load

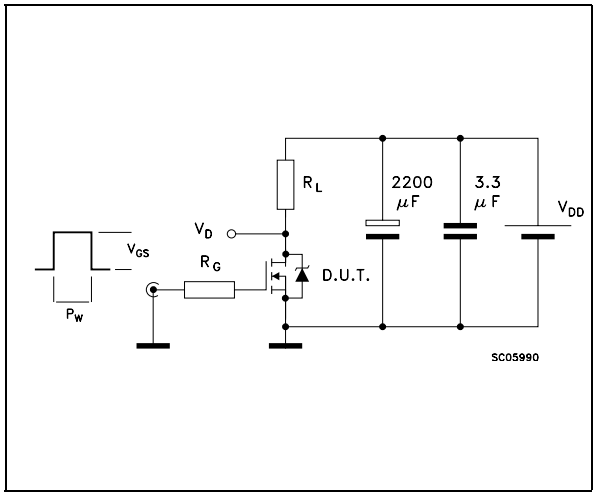


Figure 15: Test Circuit For Diode Recovery Times

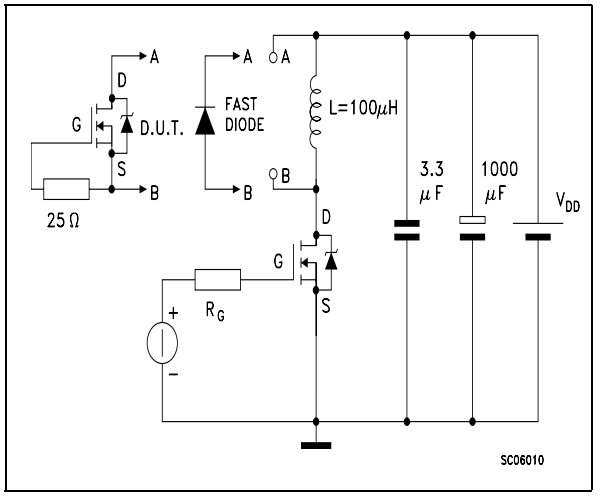
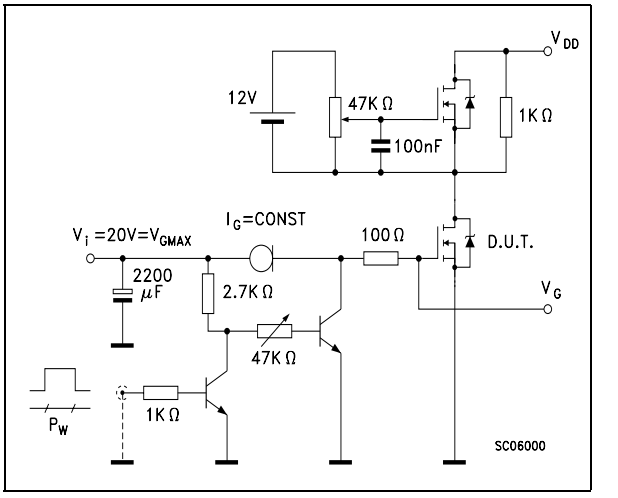
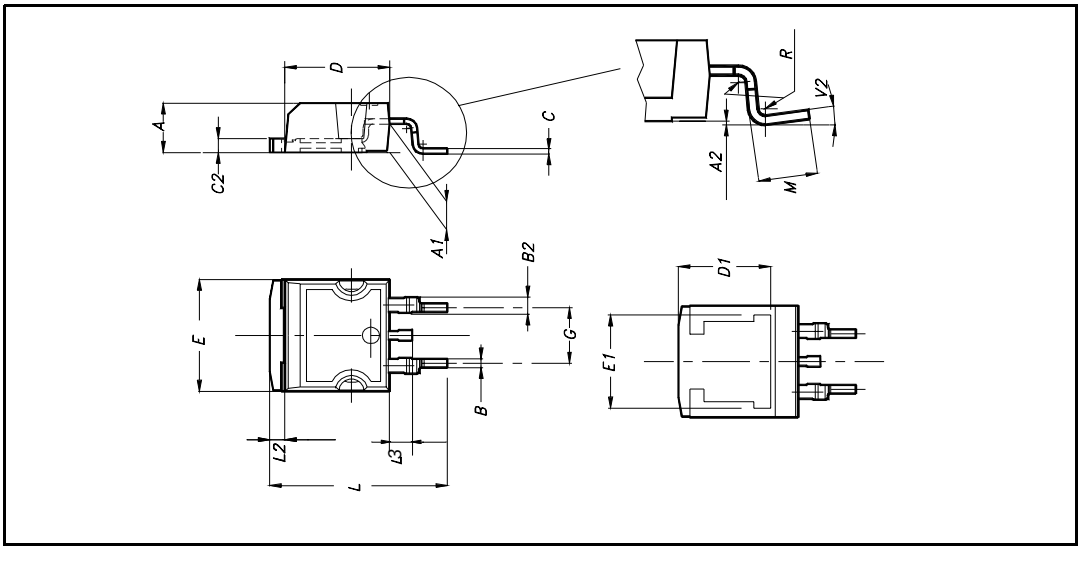


Figure 16: Gate Charge Test Circuit

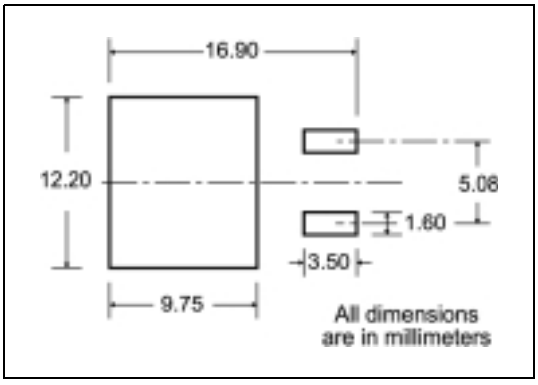


D²PAK MECHANICAL DATA

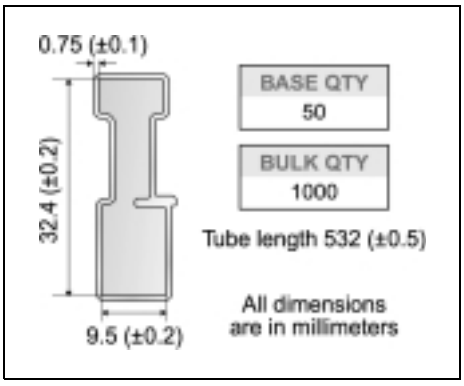
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0º		4º			



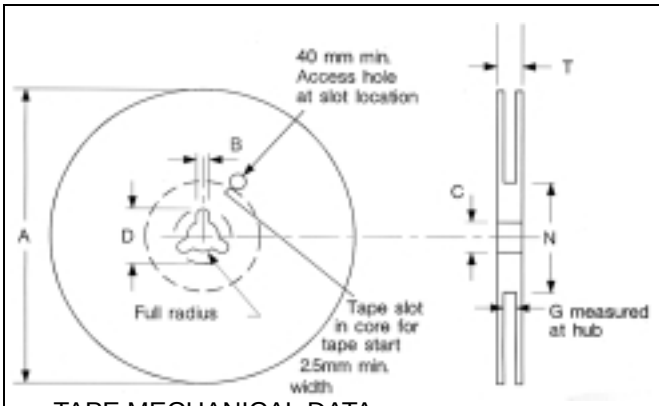
D²PAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*



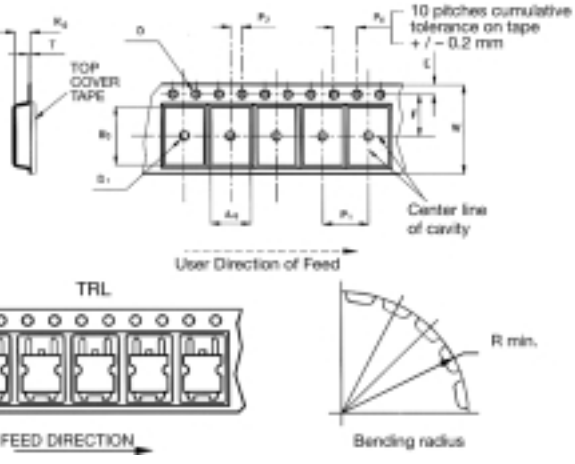
REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956



* on sales type

TO-262 (I^2PAK) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055

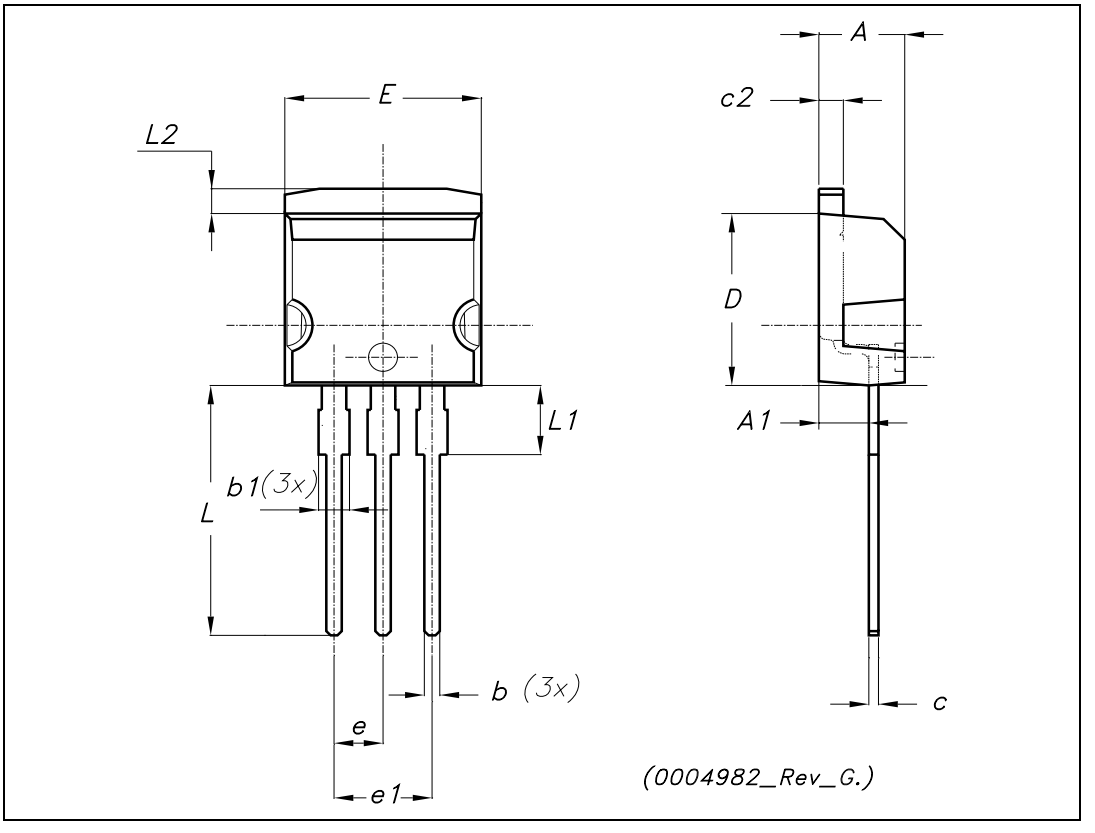


Table 11: Revision History

Date	Revision	Description of Changes
15-Feb-2005	1	First Release.